TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSII⁻⁵)

2SK1930

Chopper Regulator, DC-DC Converter, and Motor Drive Applications

• Low drain—source ON resistance : RDS (ON) = 3.0Ω (typ.) • High forward transfer admittance : $|Y_{fs}| = 2.0 S$ (typ.) • Low leakage current : $I_{DSS} = 300 \mu A$ (max) ($V_{DS} = 800 V$) • Enhancement mode : $V_{th} = 1.5 \sim 3.5 V$ ($V_{DS} = 10 V$, $I_{D} = 1 mA$)

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	1000	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	1000	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	4	A	
	Pulse (Note 1)	I _{DP}	12		
Drain power dissipation (Tc = 25°C)		PD	100	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

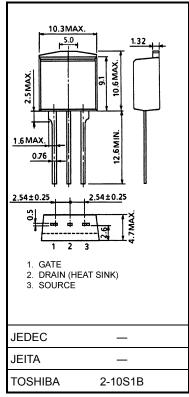
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.25	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C / W

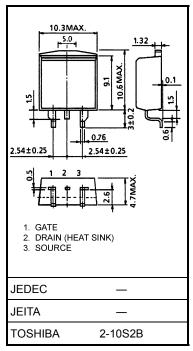
Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight: 1.5 g (typ.)



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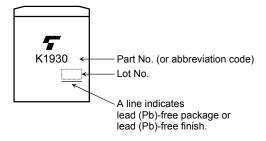
Electrical Characteristics (Ta = 25°C)

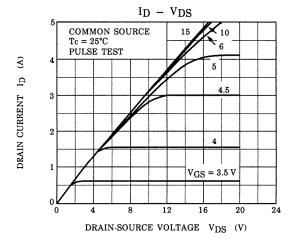
Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V	_	_	±100	nA
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 800 V, V _{GS} = 0 V	_	_	300	μΑ
Drain-source br	reakdown	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	1000	_	_	V
Gate threshold v	/oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 2 A	_	3.0	3.8	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 20 V, I _D = 2 A	1.0	2.0	_	S
Input capacitano	ce	C _{iss}		_	700	_	
Reverse transfe	r capacitance	C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	55	_	pF
Output capacitance		Coss			100	_	
Switching time	Rise time	t _r	V _{GS} 10V I I VOUT	_	18	_	
	Turn-on time	t _{on}	$^{\text{VGS}}$ $_{0\text{V}}$ $^{\text{L}}$ $^{\text{RL}}$ $^{\text{RL}}$	_	30	_	20
	Fall time	t _f	V _{DD} ≒400V	_	12		ns
	Turn-off time	toff	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \mu \text{s}$	_	70	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	60	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 4 A		35		nC
Gate-drain ("miller") charge		Q _{gd}			25	_	

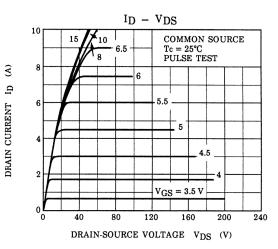
Source-Drain Ratings and Characteristics (Ta = 25°C)

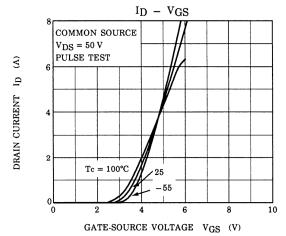
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	4	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	_	_	12	Α
Forward voltage (diode)	V _{DSF}	I_{DR} = 4 A, V_{GS} = 0 V			-1.9	V

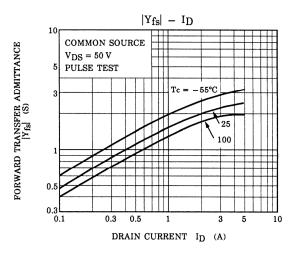
Marking

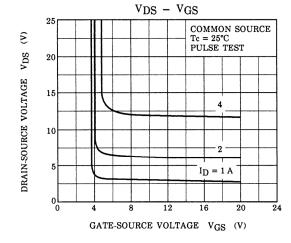


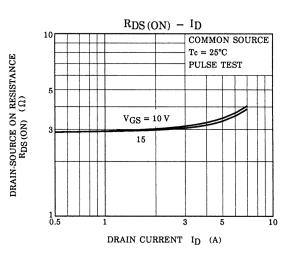




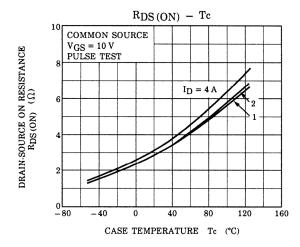


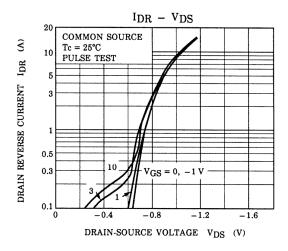


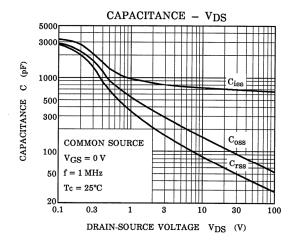


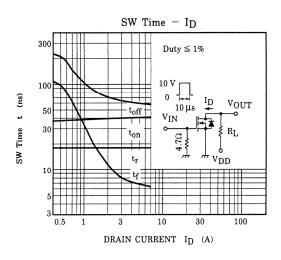


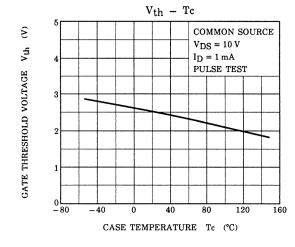
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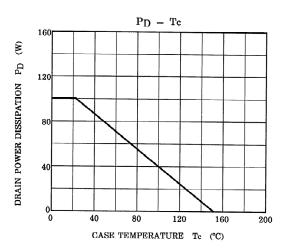


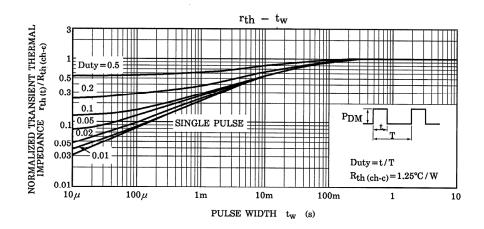


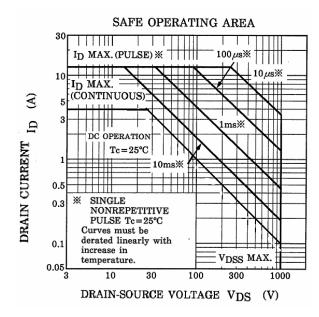












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